TOSHIBA Photocoupler GaAs Ired & Photo-Transistor

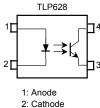
# TLP628,TLP628-2,TLP628-4

Programmable Controllers **DC-Output Module** Telecommunication

The TOSHIBA TLP628, -2, and -4 consists of a gallium arsenide infrared emitting diode optically coupled to a phototransistor which has a 350V high voltage of collector-emitter breakdown voltage. The TLP628-2 offers two isolated channels in a eight lead plastic DIP package, while the TLP628-4 provide four isolated channels per package.

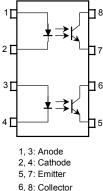
- Collector-emitter voltage: 350 V (min.) •
- Current transfer ratio: 50% (min.) •
- Isolation voltage: 5000Vrms (min.)
- UL recognized: UL1577, file No. E67349 •
- BSI approved: BS EN60065:2002, certificate no.7426 BS EN60950-1:2002, certificate no.7427

#### Pin Configurations (top view)

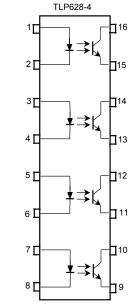


3<sup>.</sup> Emitter

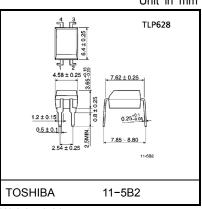
4: Collector



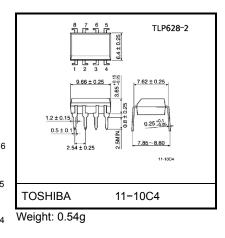
TLP628-2

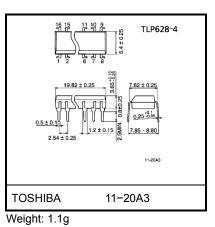


1, 3, 5, 7: Anode 2, 4, 6, 8: Cathode 9, 11, 13, 15: Emitter 10, 12, 14, 16: Collector



Weight: 0.26g





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Unit in mm

Absolute Maximum Ratings (Ta = 25°C)

			Ra		
Characteristic		Symbol	TLP628	TLP628–2 TLP628–4	Unit
Forward current		١ <sub>F</sub>	60	50	mA
	Forward current derating	ΔI <sub>F</sub> / °C	–0.7 (Ta ≥ 39°C)	–0.5 (Ta ≥ 25°C)	mA / °C
LED	Pulse forward current	I <sub>FP</sub>	1 (100µs pu	А	
	Reverse voltage	V <sub>R</sub>	Į	V	
	Junction temperature	Тj	12	°C	
	Collector-emitter voltage	V <sub>CEO</sub>	35	V	
	Emitter-collector voltage	V <sub>ECO</sub>		V	
for	Collector current	Ι <sub>C</sub>	50		mA
Detector	Collector power dissipation (1 circuit)	PC	150	100	mW
	Collector power dissipation derating (Ta ≥ 25°C, 1 circuit)	ΔP <sub>C</sub> / °C	-1.5	-1.0	mW / °C
	Junction temperature	Тj	12	°C	
Stor	rage temperature range	T <sub>stg</sub>	-55~125		°C
Ope	erating temperature range	T <sub>opr</sub>	-55~100		°C
Lead soldering temperature		T <sub>sol</sub>	260 (10s)		°C
Total package power dissipation (1 circuit)		PT	200 150		mW
Total package power dissipation derating (Ta ≥ 25°C, 1 circuit)		ΔΡ <sub>T</sub> / °C	-2.0 -1.5		mW / °C
Isolation voltage		BVS	5000 (AC, 1min., R.H. ≤ 60%) (Note 1)		Vrms

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

(Note 1) Device considered a two terminal device: LED side pins shorted together and detector side pins shorted together.

#### **Recommended Operating Conditions**

Characteristic	Symbol	Min.	Тур.	Max.	Unit
Supply voltage	V <sub>CC</sub>			200	V
Forward current	١ <sub>F</sub>	_	16	25	mA
Collector current	Ι <sub>C</sub>	_	—	10	mA
Operating temperature	T <sub>opr</sub>	-25	_	85	°C

Note: Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.

## Individual Electrical Characteristics (Ta = 25°C)

	Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
LED	Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 10 mA	1.0	1.15	1.3	V
	Reverse current	I <sub>R</sub>	V <sub>R</sub> = 5 V	_	_	10	μA
	Capacitance	CT	V = 0, f = 1 MHz	_	30	_	pF
Detector	Collector–emitter breakdown voltage	V <sub>(BR)</sub> CEO	I <sub>C</sub> = 0.1 mA	350	_	_	V
	Emitter–collector breakdown voltage	V <sub>(BR) ECO</sub>	I <sub>E</sub> = 0.1 mA	7	_	_	V
		llector dark current ICEO	V <sub>CE</sub> = 300 V	_	10	200	nA
			V <sub>CE</sub> = 300 V, Ta = 85°C	_	_	50	μA
	Capacitance collector to emitter	C <sub>CE</sub>	V = 0, f = 1 MHz	_	10	_	pF

## Coupled Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Current transfer ratio	IC / IF	I <sub>F</sub> = 5 mA, V <sub>CE</sub> = 5 V Rank GB	50	_	600	%
			100	I	600	
Saturated CTR	I <sub>C</sub> / I <sub>F (sat)</sub>	IF = 1 mA, V <sub>CE</sub> = 0.4 V Rank GB	—	60	I	%
			30	_	_	
Collector–emitter saturation voltage	V <sub>CE (sat)</sub>	I <sub>C</sub> = 2.4 mA, I <sub>F</sub> = 8 mA	_	_	0.4	
		I <sub>C</sub> = 0.2 mA, I <sub>F</sub> = 1 mA Rank GB	—	0.2	_	V
			_		0.4	

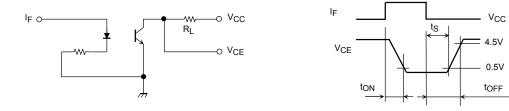
## Isolation Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Capacitance input to output	CS	V <sub>S</sub> = 0, f = 1 MHz	_	0.8	_	pF
Isolation resistance	R <sub>S</sub>	V <sub>S</sub> = 500 V R.H. ≤ 60%	5×10 <sup>10</sup>	10 <sup>14</sup>	_	Ω
		AC, 1 minute	5000	_	_	V
Isolation voltage	BVS	AC, 1 second, in oil	_	10000	_	V <sub>rms</sub>
		DC, 1 minute, in oil	—	10000	_	V <sub>dc</sub>

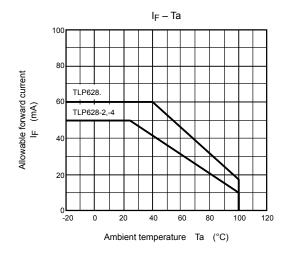
#### Switching Characteristics (Ta = 25°C)

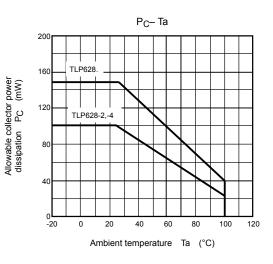
Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Rise time	tr		_	2	_	
Fall time	t <sub>f</sub>	V <sub>CC</sub> = 10 V, I <sub>C</sub> = 2 mA	_	3	_	μs
Turn–on time	t <sub>on</sub>	AR <sub>L</sub> = 100Ω	_	3	_	
Turn-off time	t <sub>off</sub>		_	3	_	
Turn–on time	t <sub>ON</sub>	R <sub>L</sub> = 1.9 kΩ (Fig.1) V <sub>CC</sub> = 5 V, I <sub>F</sub> = 16 mA	_	3	_	
Storage time	ts		_	40	_	μs
Turn-off time	tOFF		_	90	_	

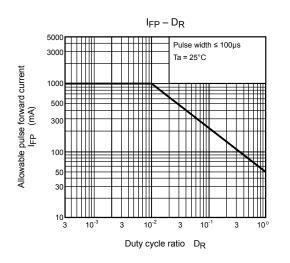
Fig. 1 Switching time test circuit

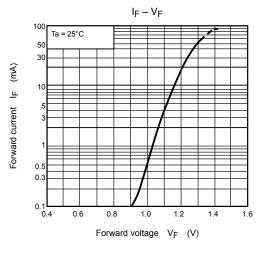


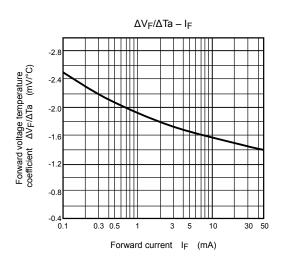
## TOSHIBA

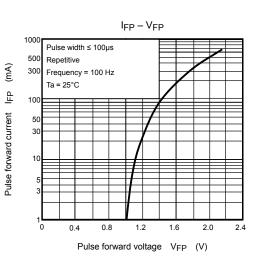




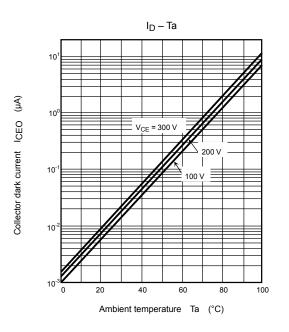








# TOSHIBA



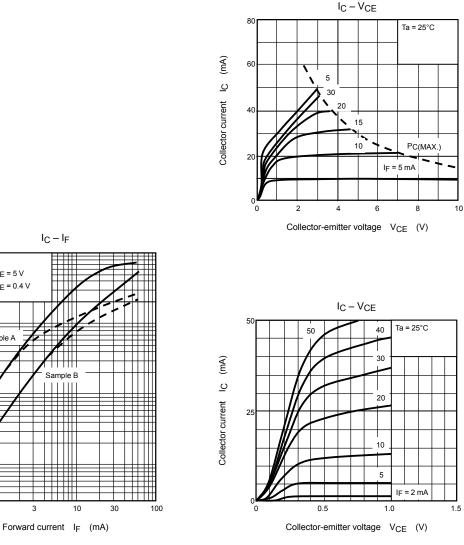
 $\mathsf{I}_{\mathsf{C}}-\mathsf{I}_{\mathsf{F}}$ 

1

Sample B

10

3





100

50

30

1(

0.5

0.3

0.

0.05

0.03 0.03 0.3

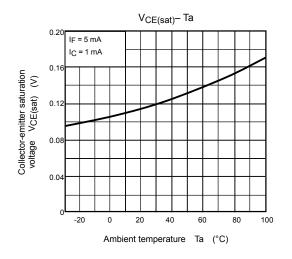
Collector current IC (mA)

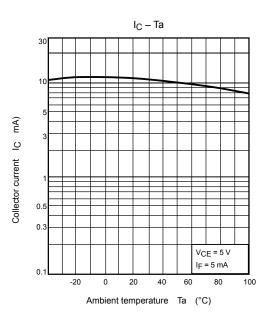
Ta = 25°C

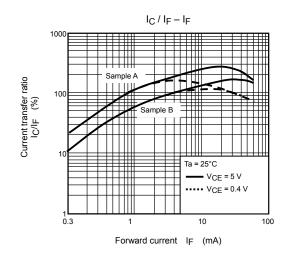
VCE = 5 V

•••••• V<sub>CE</sub> = 0.4 V

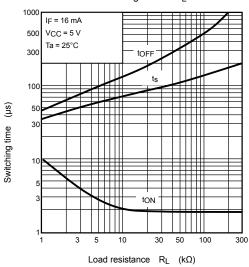
Sample A











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